

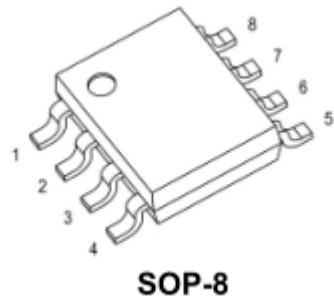
Product Summary

V_{(BR)DSS}	R_{DS(on)TYP}	I_D
30V	28mΩ@10V	5A
	42mΩ@4.5V	
-30V	38mΩ@-10V	-5A
	58mΩ@-4.5V	

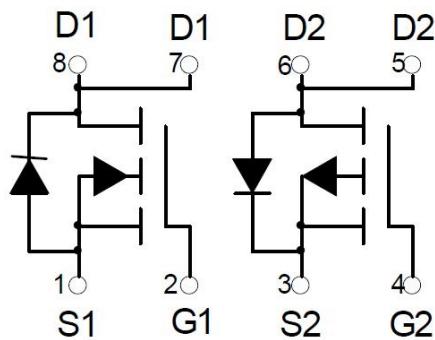
Feature

- N-Channel
 - $V_{DS} = 30V, I_D = 5A$
 - $R_{DS(ON)} < 38m\Omega @ V_{GS}=10V$
 - $R_{DS(ON)} < 55m\Omega @ V_{GS}=4.5V$
- P-Channel
 - $V_{DS} = -30V, I_D = -5A$
 - $R_{DS(ON)} < 50m\Omega @ V_{GS} = -10V$
 - $R_{DS(ON)} < 80m\Omega @ V_{GS} = -4.5V$
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

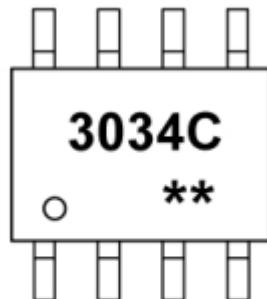
Package



Circuit diagram



Marking



Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value		Unit
		N-Channel	P-Channel	
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Continuous Drain Current $T_A=25^\circ\text{C}$	I_D	5	-5	A
Maximum Power Dissipation $T_A=25^\circ\text{C}$	P_D	2		W
Thermal Resistance from Junction to Ambient($t \leq 10\text{s}$)	$R_{\theta JA}$	62.5		$^\circ\text{C}/\text{W}$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	$-55 \sim +150$		$^\circ\text{C}$

N-Channel Electrical characteristics

($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$\text{BV}_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	30			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			± 100	μA
Gate threshold voltage ⁽¹⁾	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1	1.6	2.2	V
Drain-source on-resistance	$R_{DS(\text{on})}$	$V_{GS} = 10\text{V}, I_D = 3.2\text{A}$		28	38	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 2.8\text{A}$		42	55	
Forward transconductance ⁽¹⁾	g_{FS}	$V_{DS} = 4.5\text{V}, I_D = 2.5\text{A}$	2.5			S
Dynamic Characteristics						
Total gate charge	Q_g	$V_{DS} = 15\text{V}, V_{GS} = 10\text{V}, I_D = 3.4\text{A}$		4.5	6.7	nC
Gate-source charge	Q_{gs}	$V_{DS} = 15\text{V}, V_{GS} = 4.5\text{V}, I_D = 3.4\text{A}$		2.1	3.2	
Gate-drain charge	Q_{gd}			0.85		
Input capacitance	C_{iss}			0.65		
Output capacitance	C_{oss}	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		235		pF
Reverse transfer capacitance	C_{rss}			45		
Turn-on Delay Time	$T_{d(on)}$			17		
Turn-on Rise Time	T_r	$V_{DS} = 15\text{V}, R_L = 5.6\Omega, I_D \approx 2.7\text{A}, V_{GEN} = 4.5\text{V}, R_G = 1\Omega$		12	20	nS
Turn-Off Delay Time	$T_{d(off)}$			50	75	
Turn-Off Fall Time	t_f			12	20	
				22	35	
Source-Drain Diode Characteristics						
Continuous source-drain diode current	I_S	$T_C = 25^\circ\text{C}$			5	A
Pulse diode forward current	I_{SM}				20	A
Body diode voltage	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0\text{V}$			1.2	V

Notes:

1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
2. Guaranteed by design, not subject to production testing.



ZL MOSFET

ZL3034C

P-Channel Electrical characteristics

(T_A=25°C, unless otherwise noted)

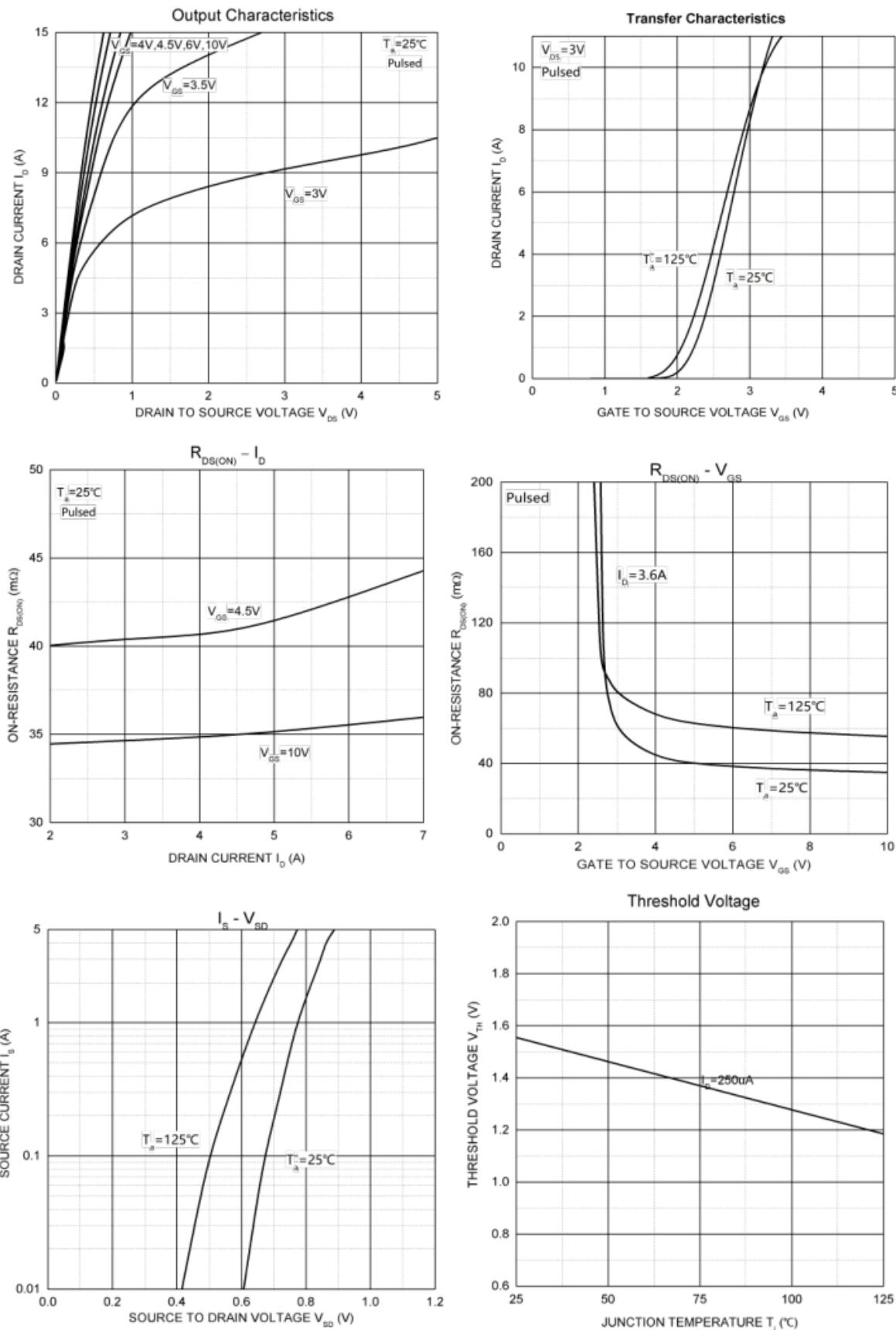
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Off characteristics						
Drain-source breakdown voltage	BV _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -24V, V _{GS} = 0V			1	uA
Gate-body leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	uA
On characteristics						
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.5	-2.0	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} = -10V, I _D = -4.1A		38	50	mΩ
		V _{GS} = -4.5V, I _D = -3A		58	80	
Switching Characteristics						
Input Capacitance	C _{iss}	V _{DS} = -15V, V _{GS} = 0V, f = 1MHz		720		pF
Output Capacitance	C _{oss}			120		
Reverse Transfer Capacitance	C _{rss}			75		
Turn-on Delay Time	T _{d(on)}	V _{DD} = -15V, I _D = -1A, V _{GS} = -10V, R _G = 3Ω, R _L = 3.6Ω		8.6		nS
Turn-on Rise Time	T _r			5.0		
Turn-Off Delay Time	T _{d(off)}			28.2		
Turn-Off Fall Time	t _f			13.5		
Source-Drain Diode Characteristics						
Body Diode Voltage	V _{SD}	I _S = -1A, V _{GS} = 0V			-1.2	V

Notes:

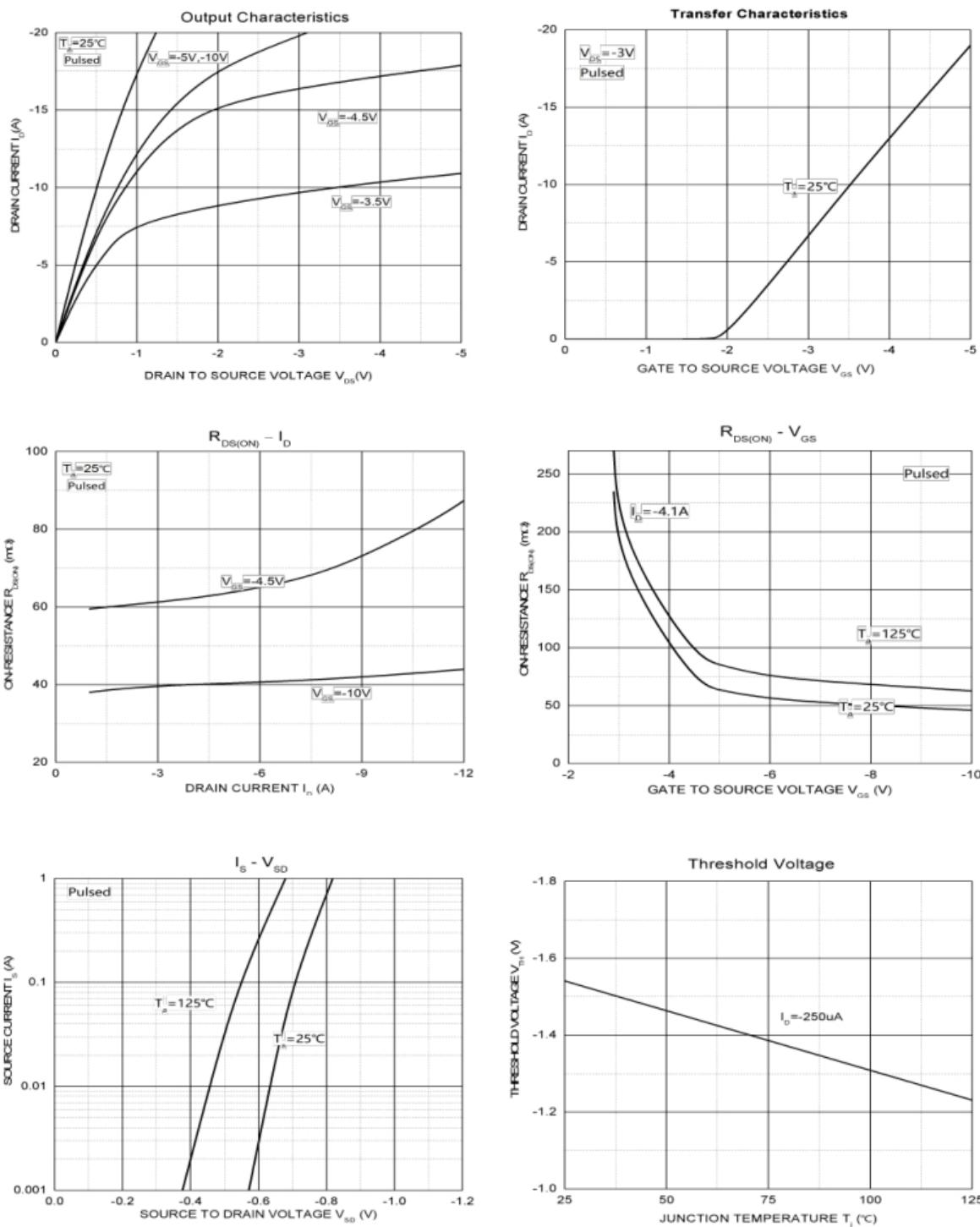
1. Guaranteed by design, not subject to production testing.

2. Pulse Test: Pulse Width ≤ 300μs, duty cycle ≤ 2%.

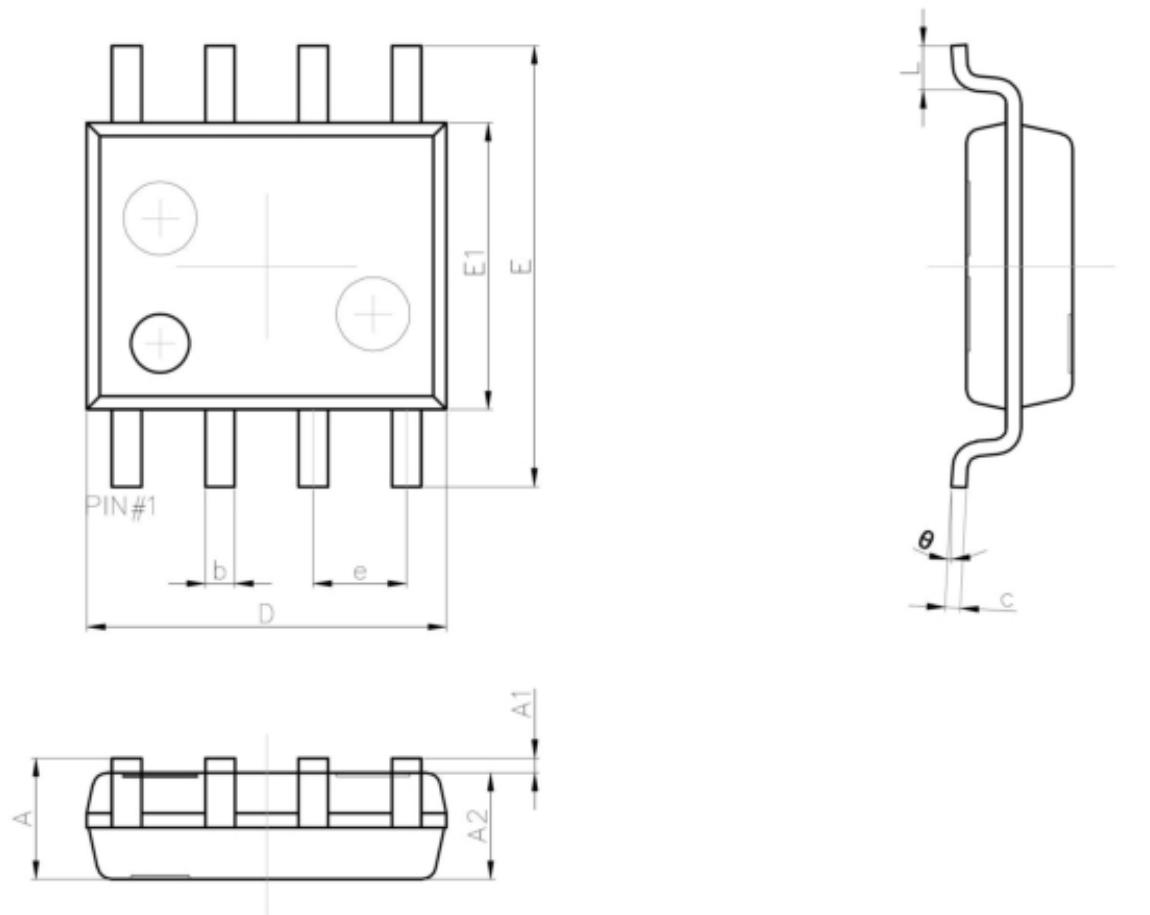
N-Channel Typical Characteristics



P-Channel Typical Characteristics



SOP-8 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.35	1.75
A1	0.10	0.25
A2	1.35	1.55
b	0.33	0.51
c	0.17	0.25
D	4.80	5.00
e	1.27 REF.	
E	5.80	6.20
E1	3.80	4.00
L	0.40	1.27
θ	0°	8°